

TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (U-MOSIII)

TPC8112

TENTATIVE

Lithium Ion Battery Applications
Notebook PC Applications
Portable Equipment Applications

- Small footprint due to small and thin package
- Low drain-source ON resistance: $R_{DS(ON)} = 5.0\text{m}\Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 31\text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = -10\text{ }\mu\text{A}$ (max) ($V_{DS} = -30\text{ V}$)
- Enhancement-mode: $V_{th} = -0.8$ to -2.0 V ($V_{DS} = -10\text{ V}$, $I_D = -1\text{ mA}$)

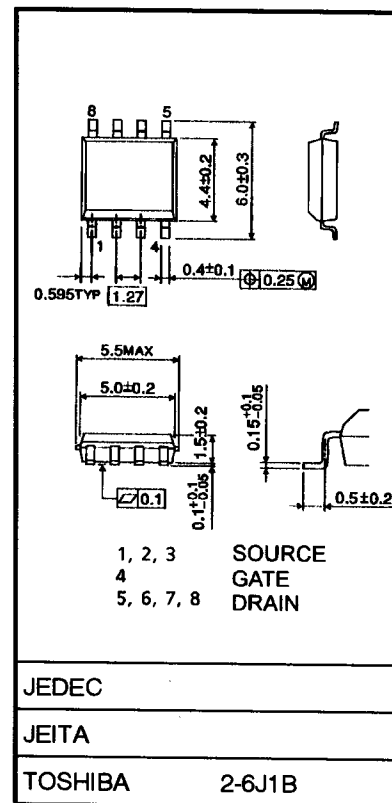
Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-30	V
Drain-gate voltage ($R_{GS} = 20\text{ k}\Omega$)		V_{DGR}	-30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	-13	A
	Pulse (Note 1)	I_{DP}	-52	
Drain power dissipation ($t = 10\text{ s}$) (Note 2a)		P_D	1.9	W
Drain power dissipation ($t = 10\text{ s}$) (Note 2b)		P_D	1.0	W
Single pulse avalanche energy (Note 3)		E_{AS}	219	mJ
Avalanche current		I_{AR}	-13	A
Repetitive avalanche energy (Note 2a) (Note 4)		E_{AR}	0.19	mJ
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

Note: For (Note 1), (Note 2), (Note 3) and (Note 4), please refer to the next page.

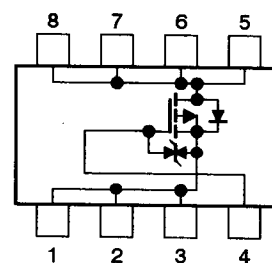
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.080 g (typ.)

Circuit Configuration

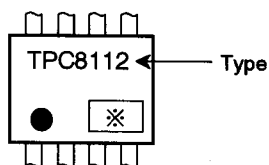


Thermal Characteristics

TENTATIVE

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th(ch-a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th(ch-a)}$	125	°C/W

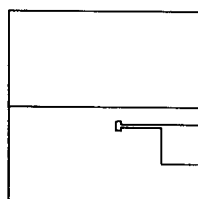
Marking (Note 5)



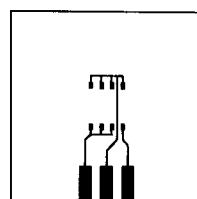
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:

(a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



(a)



(b)

Note 3: $V_{DD} = -24\text{ V}$, $T_{ch} = 25^\circ\text{C}$ (initial), $L = 1.0\text{ mH}$, $R_G = 25\ \Omega$, $I_{AR} = -13\text{ A}$

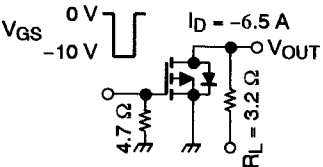
Note 4: Repetitive rating; pulse width limited by maximum channel temperature

Note 5: • on lower left of the marking indicates Pin 1.

※ shows lot number. (year of manufacture: last decimal digit of the year of manufacture, month of manufacture: January to December are denoted by letters A to L respectively.)

Electrical Characteristics (Ta = 25°C)

T E N T A T I V E

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	—	—	±10	μA
Drain cut-OFF current		I _{DSS}	V _{DS} = -30 V, V _{GS} = 0 V	—	—	-10	μA
Drain-source breakdown voltage		V _(BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-30	—	—	V
		V _(BR) DSX	I _D = -10 mA, V _{GS} = 20 V	-15	—	—	
Gate threshold voltage		V _{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8	—	-2.0	V
Drain-source ON resistance		R _{DS} (ON)	V _{GS} = -4 V, I _D = -6.5 A	—	9.0	14	mΩ
			V _{GS} = -10 V, I _D = -6.5 A	—	5.0	6.0	
Forward transfer admittance		Y _{fs}	V _{DS} = -10 V, I _D = -6.5 A	15.5	31	—	S
Input capacitance		C _{iss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	—	5880	—	pF
Reverse transfer capacitance		C _{rss}		—	1000	—	
Output capacitance		C _{oss}		—	1050	—	
Switching time	Rise time	t _r	 V_{DD} = -15 V Duty ≤ 1%, t_w = 10 μs	—	11	—	ns
	Turn-ON time	t _{on}		—	22	—	
	Fall time	t _f		—	110	—	
	Turn-OFF time	t _{off}		—	395	—	
Total gate charge (gate-source plus gate-drain)		Q _g	V _{DD} ≈ -24 V, V _{GS} = 10 V, I _D = -13 A	—	130	—	nC
Gate-source charge 1		Q _{gs1}		—	10	—	
Gate-drain ("miller") charge		Q _{gd}		—	30	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain reverse current	Pulse (Note 1)	I_{DRP}	—	—	—	-52	A
Forward voltage (diode)		V_{DSF}	$I_{DR} = -13 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.2	V

T E N T A T I V E

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